

FIG. 1

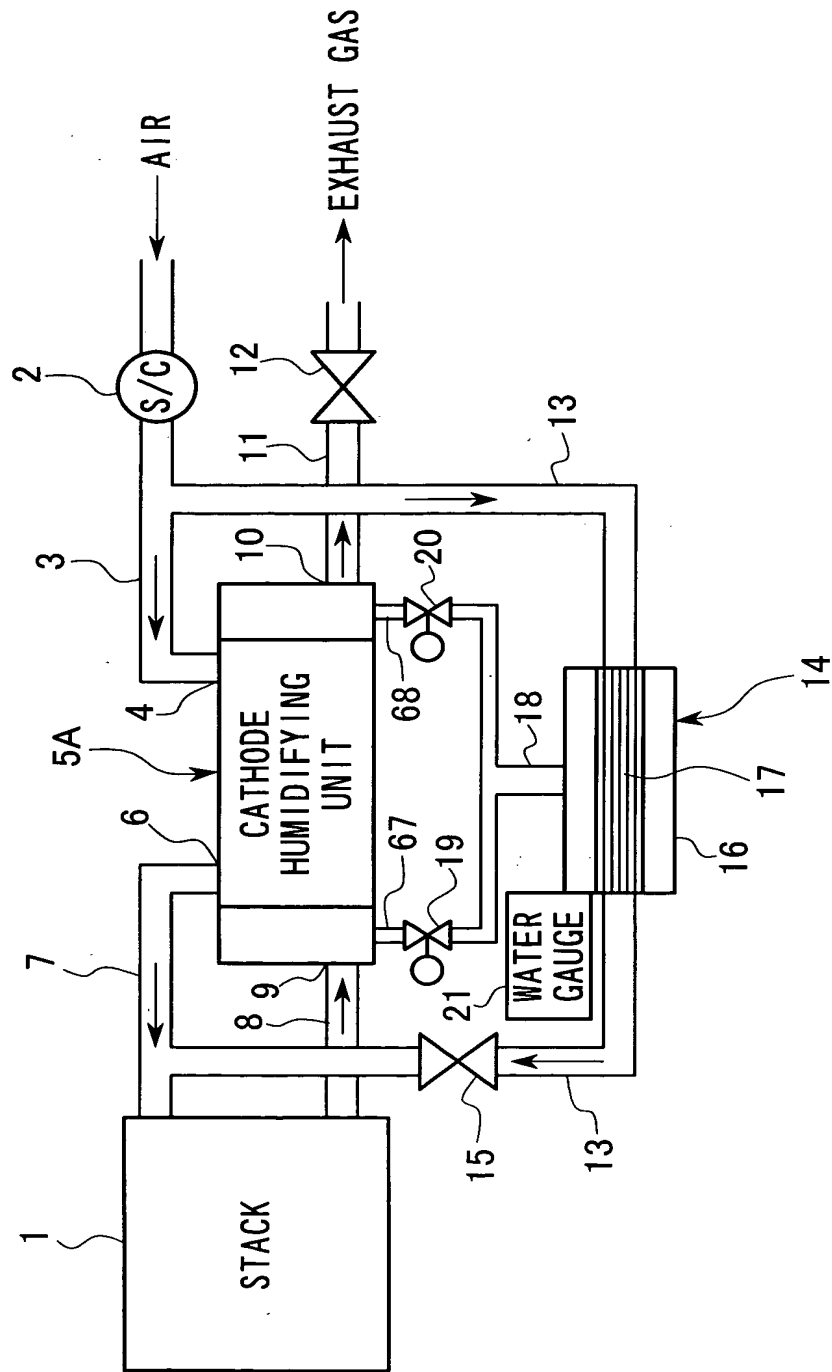


FIG. 2

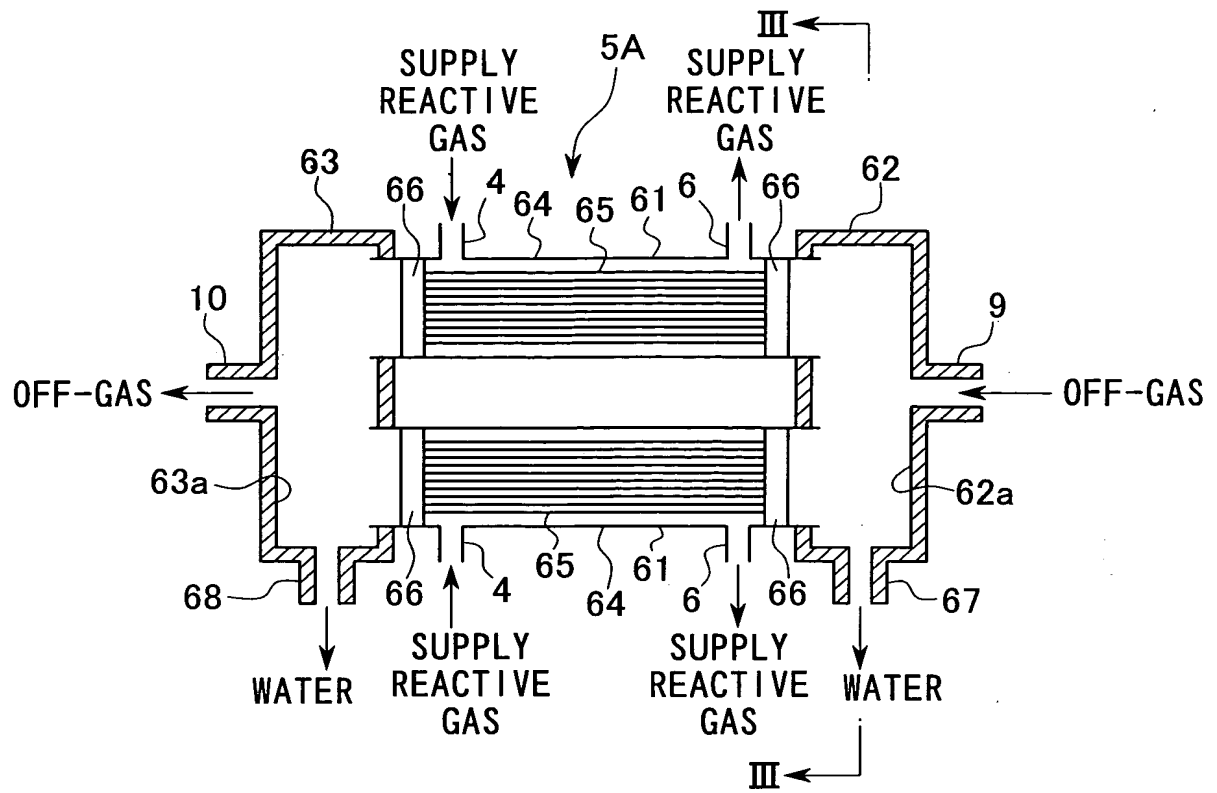


FIG. 3

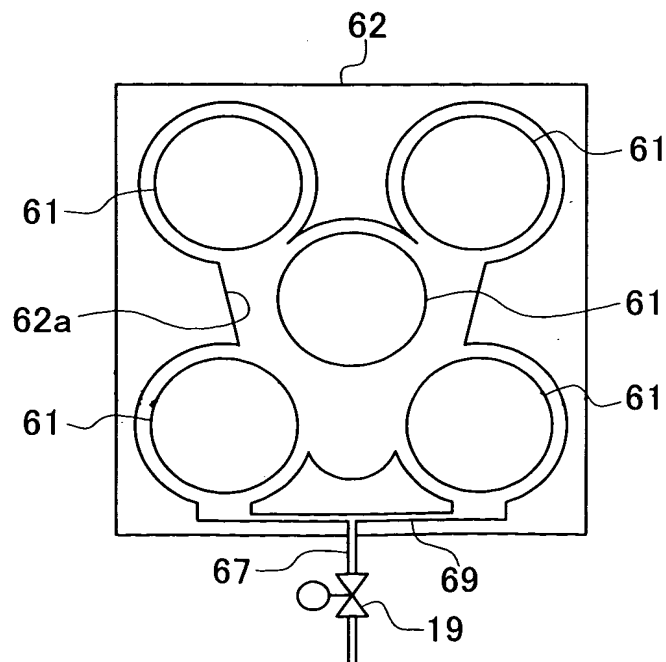


FIG. 4

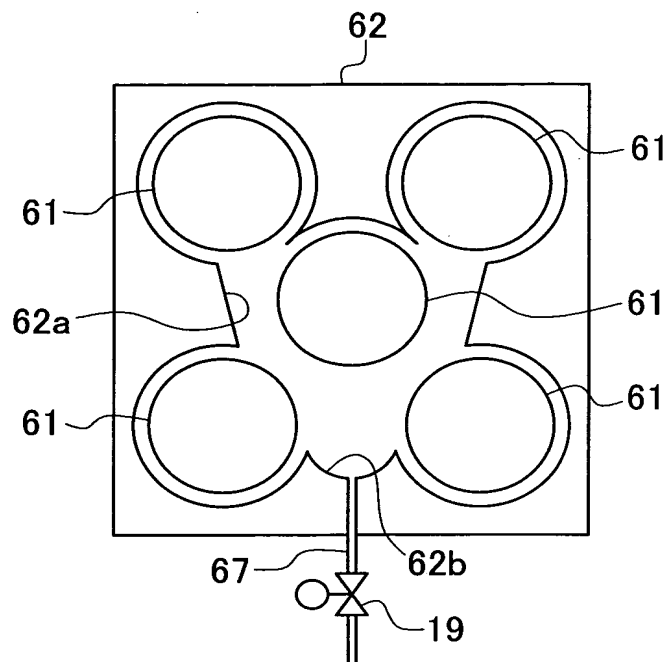


FIG. 5

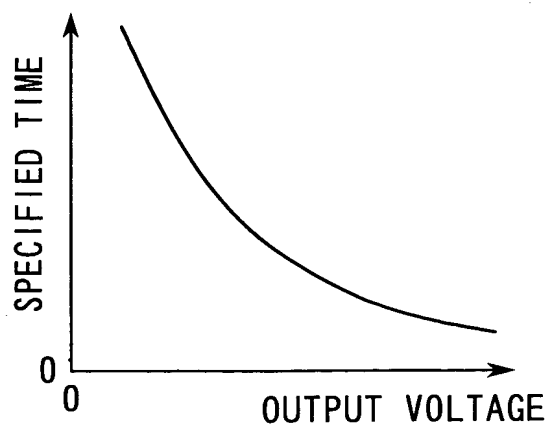


FIG. 6

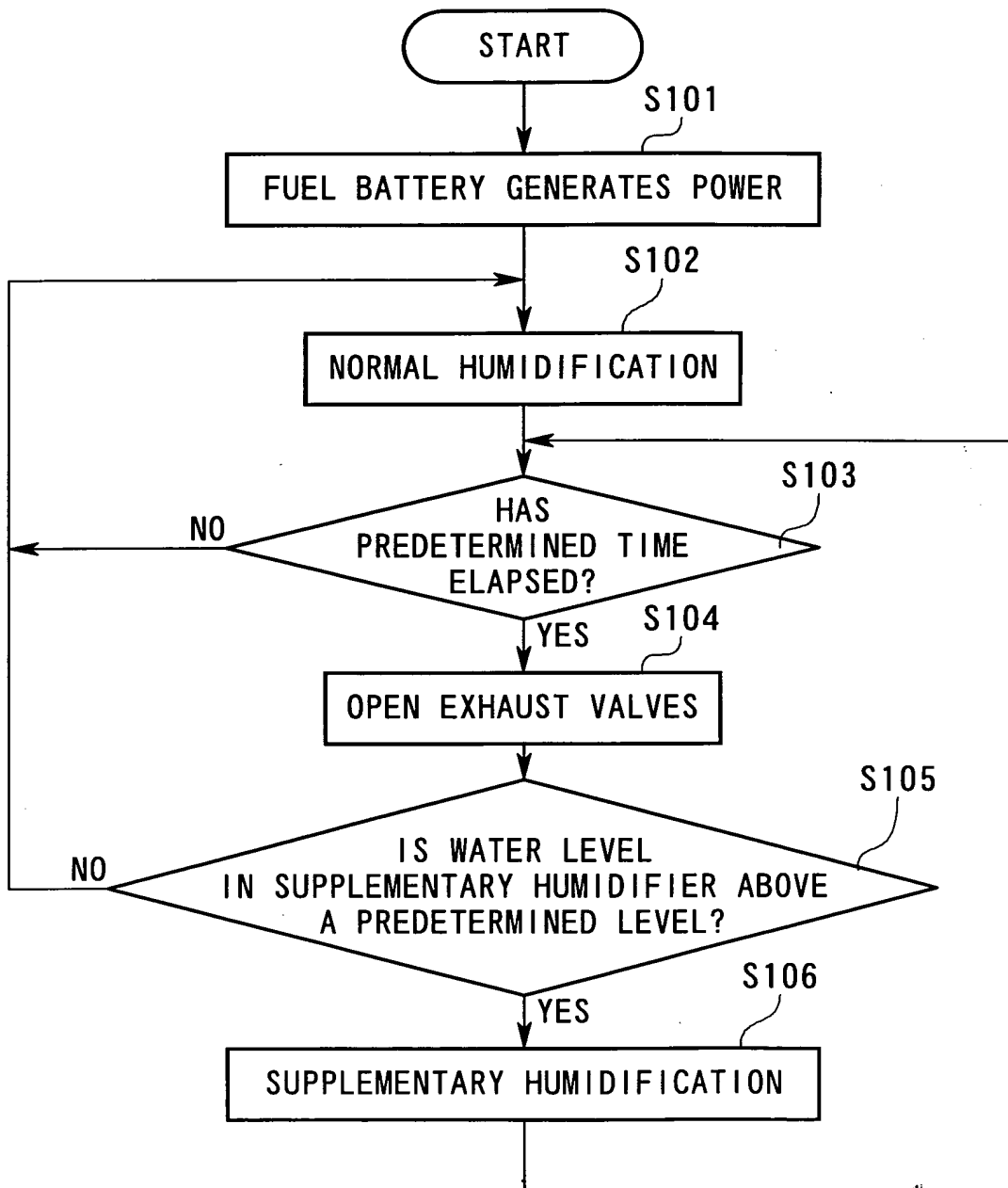


FIG. 7

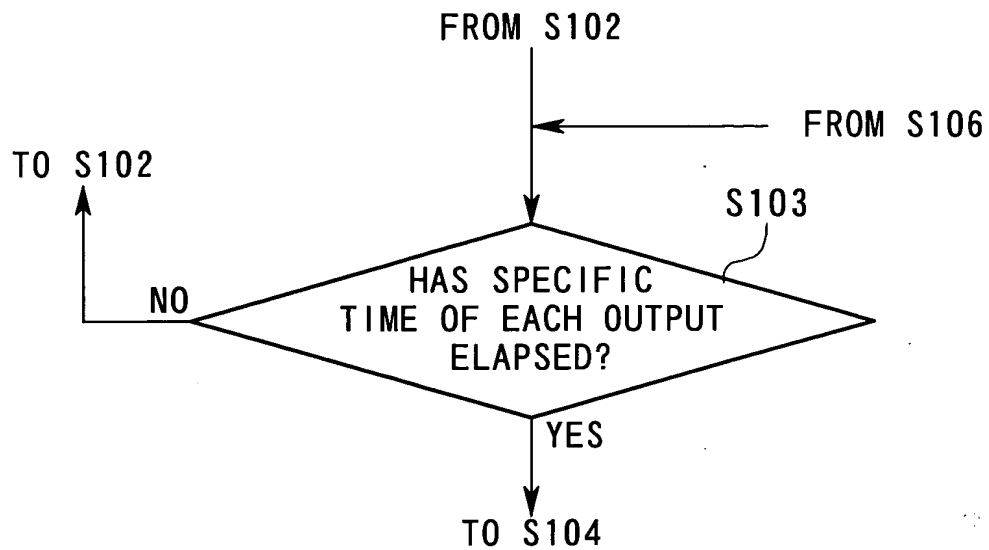


FIG. 8

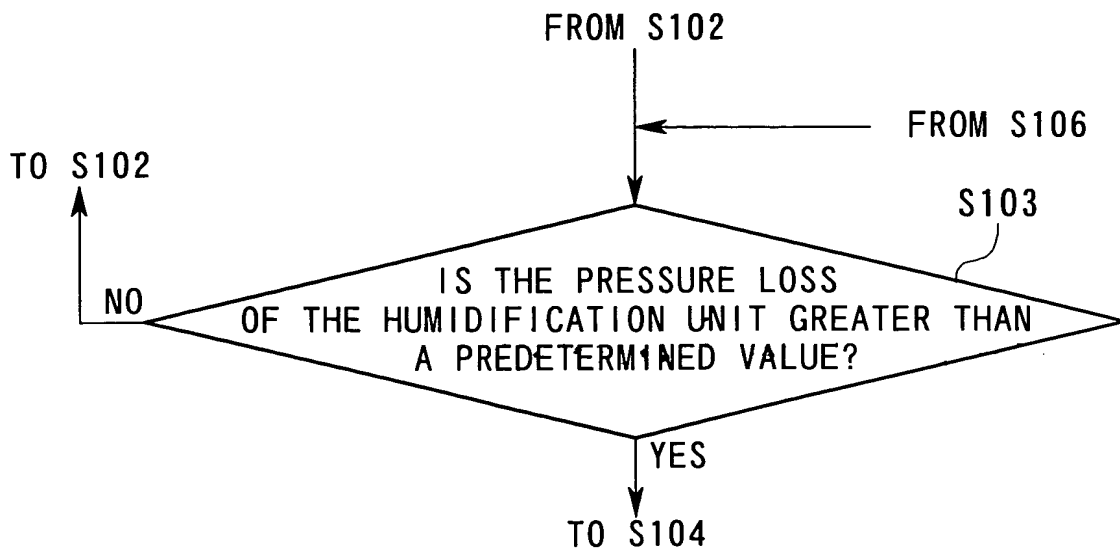


FIG. 9

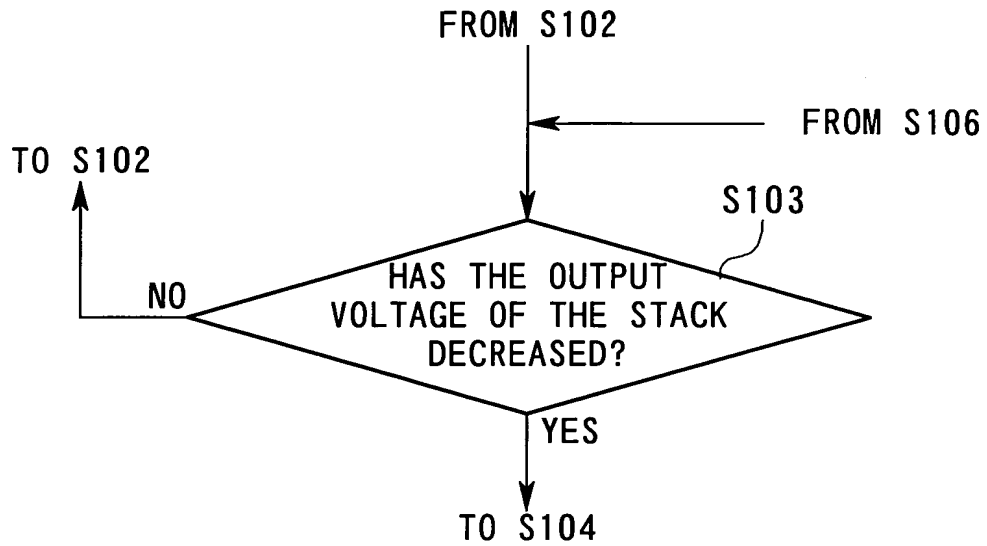


FIG. 10

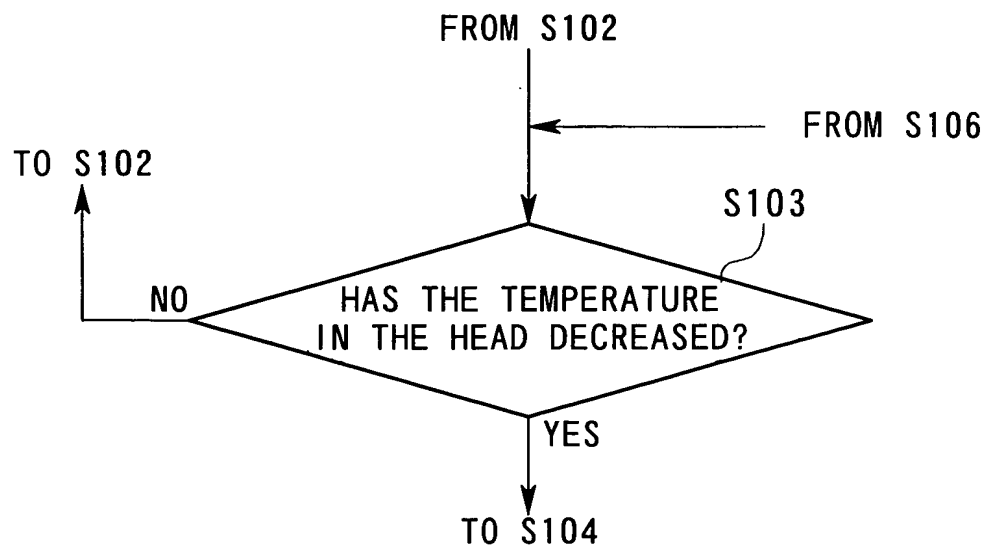




FIG. 12

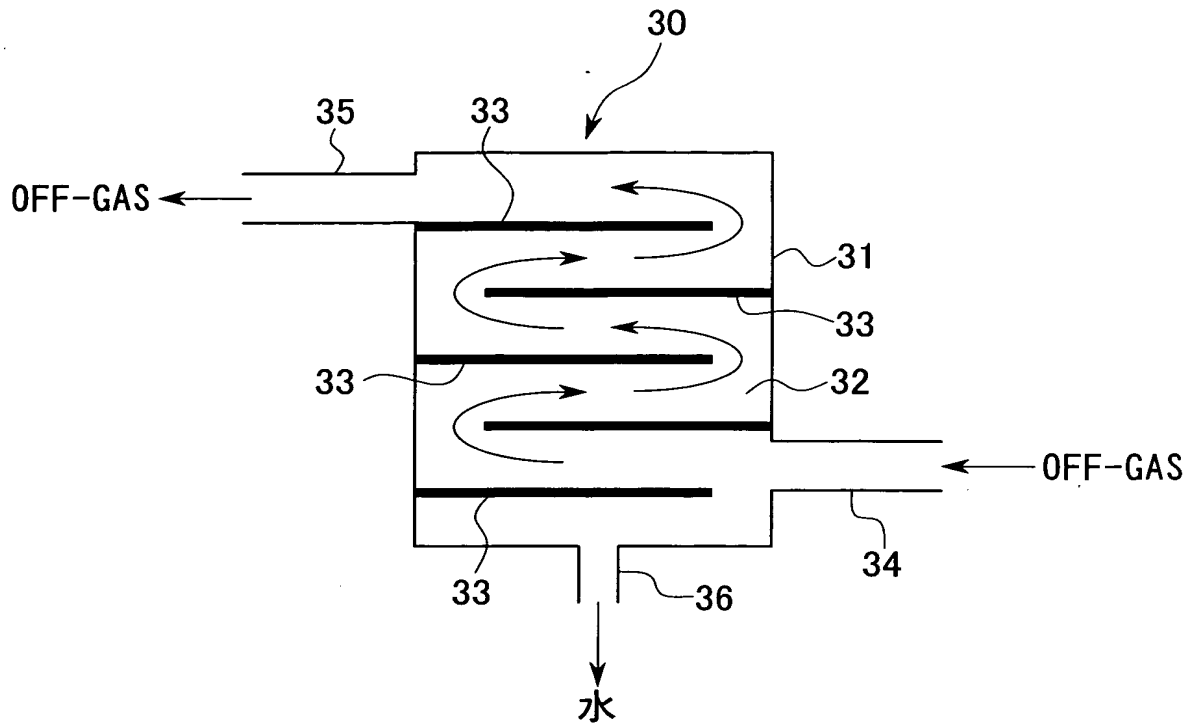




FIG. 13

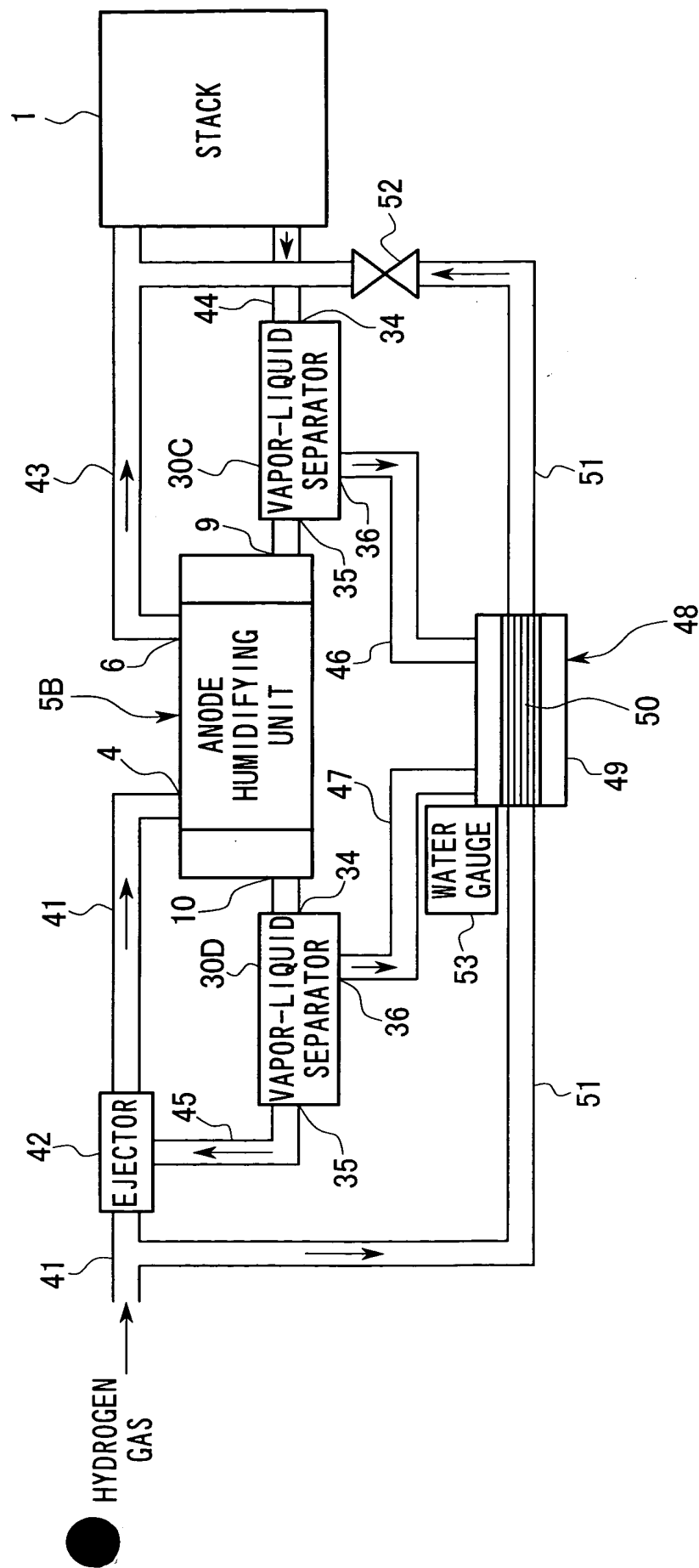


FIG. 14

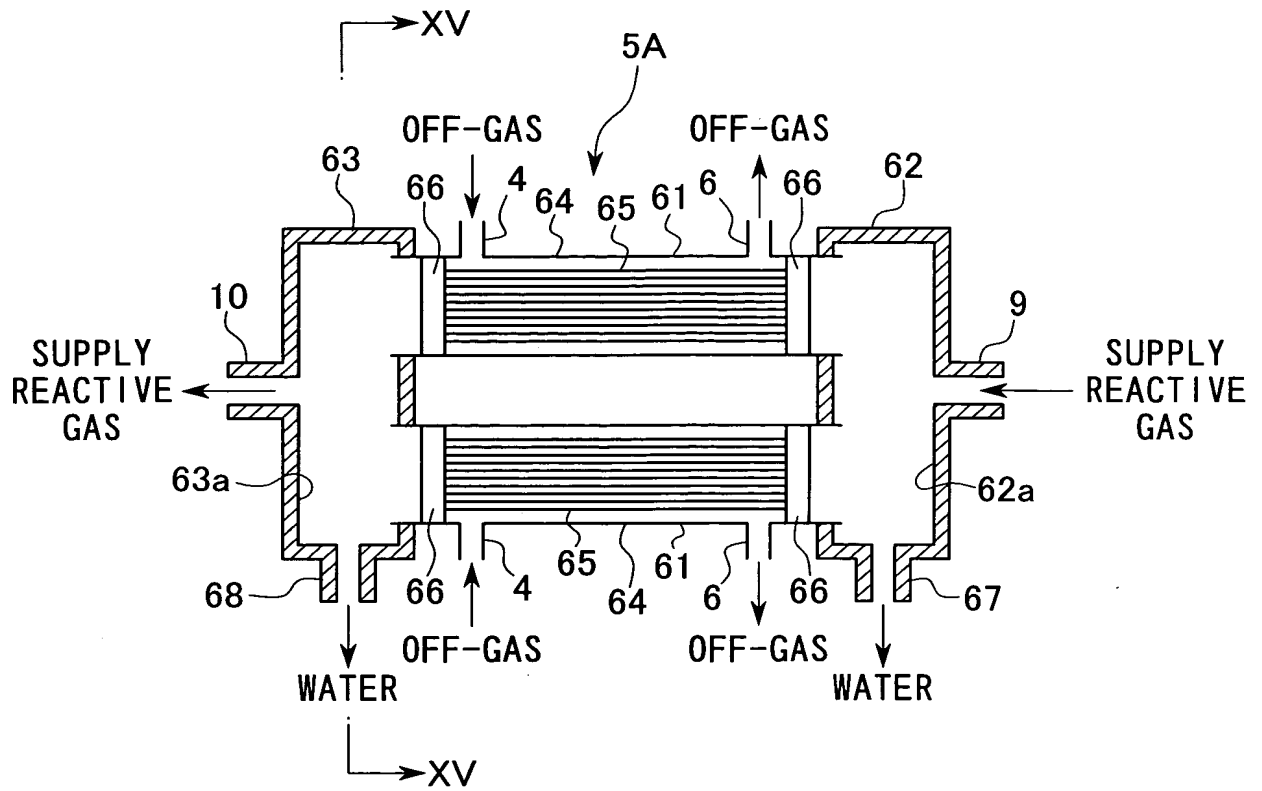
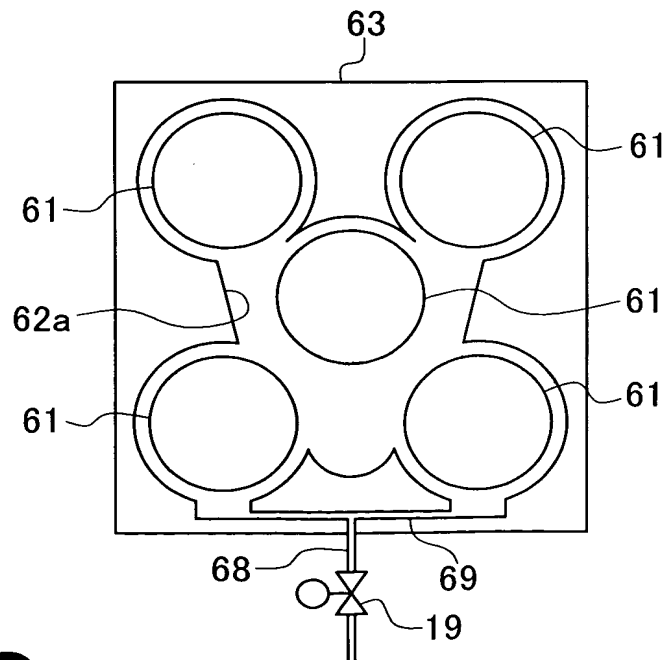


FIG. 15





This diagram shows a cross-sectional view of a second embodiment of the semiconductor device. It features a central substrate 80 with a central layer 94. Above the substrate is a first conductive layer 91, and below it is a second conductive layer 91. The substrate is flanked by two side regions 92 and 93. Gas supply ports 97a and 97b are located on the top and bottom surfaces of the substrate. Arrows indicate the flow of "SUPPLY REACTIVE GAS" into the device and "OFF-GAS" out of the device. The central layer 94 is shown with horizontal hatching, and the conductive layers 91 are shown with vertical hatching.